

Substitute for form 1449A&B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(Use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	10/757,770
				Filing Date	January 14, 2004
				First Named Inventor	Yuan, Zheng
				Art Unit	1792
Examiner Name	Kelly M. Stouffer				
Sheet	1	of	7	Attorney Docket Number	016301-052200US

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number Kind Code <sup>2</sup> (if known)			
	AA	US-2,861,009	11-01-1958	Rubner	
	AB	US-2,889,704	08-01-1959	Pekarek	
	AC	US-2001-0019860	09-06-2001	Adachi et al.	
	AD	US-2002-0000195	01-03-2002	Bang et al.	
	AE	US-2002-0000196	01-03-2002	Park	
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	AH	US-2002-0011215	01-31-2002	Tel et al.	
	AI	US-2002-0006729	01-2002	Geiger et al.	
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	AN	US-2003-0022523	01-01-2003	Irimo et al.	
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	AQ	US-2003-0071304	04-17-2003	Ogie, Jr., et al.	
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	AS	US-2003-0089314	05-01-2003	Matsuki et al.	
	AT	US-2003-0104677	06-01-2003	Park et al.	
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	BE	US-2004-0216844	11-01-2004	Janakiraman et al.	
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	BG	US-2005-0064730 A1	03-24-2005	Ingle et al.	
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	CG	US-5,482,858	02-01-1996	Bose et al.	
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	CK	US-5,660,472	08-26-1997	Peuse et al.	
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	DG	US-6,140,242	10-31-2000	Oh et al.	
	DH	US-6,149,987	11-21-2000	Perng et al.	
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	DK	US-6,156,114	12-05-2000	Bell et al.	
	DL	US-6,171,901	01-09-2001	Blair et al.	
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	DM	US-6,184,155	02-06-2001	Yu et al.	
	DN	US-6,190,973	02-20-2001	Berg et al.	
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	DP	US-6,197,705	03-06-2001	Vassiliev	
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	DS	US-6,217,658	04-17-2001	Orczyk et al.	
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	EM	US-6,479,405	11-12-2002	Lee et al.	
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	EO	US-6,527,910	03-04-2003	Rossmann	
	EP	US-6,541,367	04-01-2003	Mandal	
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	ES	US-6,583,069 B1	6-2003	Vassilev et al.	
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	EV	US-6,617,259 B1	09-2003	Jung et al.	
	EW	US-6,624,091	09-26-2003	Yuan	
	EX	US-6,677,712	01-01-2004	Katz et al.	
	EY	US-6,713,127 B2	03-30-2004	Subramony et al.	
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	FB	US-6,740,601	05-25-2004	Tan et al.	
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	FF	US-6,905,940	06-14-2005	Ingle et al.	
	FG	US-6,943,091	09-13-2005	Yu et al.	
	FH	US-6,946,358	09-01-2005	Doris et al.	
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	FL	US-7,208,425	04-24-2007	Ingle et al.	
	FM	US-7,335,609 B2	02-26-2008	Ingle et al.	

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		Country Code <sup>3</sup>	Number <sup>4</sup> Kind Code <sup>5</sup> (if known)				
	FN	CA	479107	12-04-1951	Goodrich Co.		<input type="checkbox"/>
	FO	EP	0520519 A1	12-30-1992	Applied Materials, Inc.		<input type="checkbox"/>
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	FP	JP	01283375	A	11-14-1989	Fujitsu Ltd.		<input type="checkbox"/>
	FQ	JP	01294868	A	11-28-1989	Nippon Electric Co. et al.		<input type="checkbox"/>
	FR	JP	4154116	A	05-27-1992	Fujitsu		<input type="checkbox"/>
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	FT	TW	479315	A	03-11-2002	Applied Materials, Inc.		<input type="checkbox"/>
	FU	WO	9925895	A1	05-27-1999	Symetrix Corp.		<input type="checkbox"/>

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>	
	FV	Applied Materials Website Printout: "SACVD (Sub-Atmospheric Chemical Vapor Deposition)*" from <a href="http://www.appliedmaterials.com/products/sacvd.html">www.appliedmaterials.com/products/sacvd.html</a> , printed 06/20/2003.	<input type="checkbox"/>	
	FW	BAKER, F. et al. "STI TEOS Densification for Furnaces and RTP Tools" 1999 IEEE/SEMI Advanced Semiconductor Manufacturing Conference, 1999, pp. 394-399.	<input type="checkbox"/>	
	FX	Bang et al. (Jan. 3 , 2002). US Patent Application Publication US-2002-0000195 A1.	<input type="checkbox"/>	
	FY	Definitions of "furnace", Merriam-Webster Online, 2006	<input type="checkbox"/>	
	FZ	Fujino, K. et al., "Dependence Of Deposition Characteristics On Base Materials In TEOS And Ozone CVD At Atmospheric Pressure," J. Electrochem Soc., Vol. 138, No. 2, pp. 550-554, February 1991	<input type="checkbox"/>	

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	GA	Kuo, Yue, "Etch Mechanism In The Low Refractive Index Silicon Nitride Plasma-Enhanced Chemical Vapor Deposition Process," Appl. Phys. Lett., Vol. 63, No. 2, pp. 144-146, July 12, 1993	<input type="checkbox"/>
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	GC	Lassig, Stephan E. et al., "Intermetal Dielectric Deposition By Electron Cyclotron Resonance Chemical Vapor Deposition (ECR CVD)," pp. cover and 1-21, no date	<input type="checkbox"/>
	GD	Li, Junling et al., "Modeling Studies Of The Mechanisms In Biased ECR CVD," 3 pages, no date	<input type="checkbox"/>
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